

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-8 (canceled).

9. (presently amended) A heat treating method comprising the steps of distributing ~~defects~~ oxide precipitates in a silicon single crystal wafer, said wafer comprising a surface region of up to several tens of μm deep from a wafer surface and ~~an adjacent central region,~~ a bulk region of several tens or more of μm deep from the wafer surface, said wafer having been prepared from a ~~perfect~~ crystal free from grown-in defects and produced by a Czochralski method, said ~~defects~~ oxide precipitates being uniformly distributed in a the bulk region consisting essentially of the central region, said heat treating method consisting of ~~by~~ a first step of maintaining a first heat treatment temperature for an initial entry of the silicon single crystal wafer up to 500°C , and a second step of maintaining a temperature ramping rate in a temperature range from the first heat treatment temperature to a second heat treatment temperature of 700°C - 900°C , said ramping rate being $1^{\circ}\text{C}/\text{min}$ or less, said first step being performed first after a wafer slicing process.

10. (presently amended) A heat treating method comprising the steps of distributing oxide precipitates ~~defects~~ in a silicon single crystal wafer, said wafer comprising a surface region of up to several tens of μm deep and ~~an adjacent central region,~~ a bulk region of several tens or more of μm deep from the wafer surface, said wafer having been prepared from a ~~perfect~~ crystal free from grown-in defects and produced by a Czochralski method, said ~~defects~~ oxide precipitates being uniformly distributed in the bulk a region ~~consisting essentially of the central region~~ said heat treating method consisting of ~~by~~ a first step of maintaining a first heat treatment temperature for an initial entry of the silicon single crystal wafer up to 500°C , and a second step of maintaining a temperature ramping rate in a temperature range from the first heat treatment temperature to a second heat treatment temperature of 700°C - 900°C , said ramping rate being $1^{\circ}\text{C}/\text{min}$ or less, so as to make

uniform the distribution of an oxide precipitate density of the silicon single crystal wafer in the wafer, said first step being performed first after a wafer slicing process.

11. (presently amended) A heat treating method comprising the steps of distributing ~~defects~~ oxide precipitates in a silicon single crystal wafer, said wafer comprising a surface region of up to several tens of μm deep and an adjacent central region, a bulk region of several tens or more of μm deep from the wafer surface, said wafer having been prepared from a ~~perfect~~ crystal free from grown-in defects and produced by a Czochralski method, said ~~defects~~ oxide precipitates being uniformly distributed in a the bulk region ~~consisting essentially of the central region~~ said heat treating method consisting of ~~by~~ a first step of controlling a first heat treatment temperature for an initial entry of the silicon single crystal wafer to be a target of the heat treatment and a second step of controlling a temperature ramping rate from the heat treatment temperature at initial entry to a higher second heat treatment temperature and maintaining in a range of 700°C - 900°C so as to make the distribution of an oxide precipitate density of the silicon single crystal wafer more uniform after heat treatment, said first step being performed first after a wafer slicing process.

12. (original) The method according to Claim 9, wherein the oxygen concentration of the perfect crystal is 13×10^{17} atoms/ cm^3 or less.

13. (previously amended) A silicon single crystal wafer produced by the method according to Claim 12.

Claims 14-23 (canceled).